

Schoop - AMSC

RABiTS provides a simple architecture

Substrate surface sufficiently smooth as processed

Three buffer layers ($\text{CeO}_2/\text{YSZ}/\text{Y}_2\text{O}_3$) - high rate reactive sputter deposition

Thin buffer stack required to contain Ni-W diffusion; < 250 nm total

Buffer stack improves over Ni/W texture ~ 1 deg.

Scalable in width for cost effective manufacturing

10 cm RABiTS with full texture, > 100 m length

4 cm RABiTS buffer process

Performance

272 A/cm-w over 10 m

380 A/cm-w short results

Mechanical strength of neutral axis conductors meet requirements for most applications

Hou - SuperPower

Substrate electropolishing

Typical speed = 40 m/h $R_a = 0.7$ nm

Demonstrated speed = 60 m/h

IBAD

Helix tape handling approach adopted - better uniformity

YSZ 15 ea, > 100 m tapes produced, ave. tex. $\sim 10.6^\circ$, low STD
MOCVD YBCO = 104 A/cm on 97 m

MgO 135 m tapes, 50 micron substrates @ 10 m/h $\Delta\Phi = 7 - 8^\circ$.
10 X faster than IBAD YSZ, with 11 X smaller deposition area.
MOCVD YBCO = 220 A/cm, 50 micron substrate, $J_e = 36$ kA/cm²,
 $I_c > 250$ A/cm (0.8 m)

Directions

Reduce # IBAD MgO template layers

Tailor MgO architecture for MOCVD

High-speed reactive sputtering of all layers

Parans - ORNL

MOD Buffer materials

Identified $\text{CeO}_2/\text{La}_2\text{Zr}_2\text{O}_7$ as multi-functional buffers on Ni/W
Very good texture using 4 cm wide RTR processing

AMSC MOD YBCO

$I_c = 213 \text{ A/cm}$ on AMSC $\text{CeO}_2/\text{YSZ}/\text{MOD La}_2\text{Zr}_2\text{O}_7/\text{NiW}$
 $I_c = 140 \text{ A/cm}$ on MOD $\text{CeO}_2/\text{MOD La}_2\text{Zr}_2\text{O}_7/\text{NiW}$

Directions

Target of 300 A/cm
100-200 nm thick single LZO coat
Meter lengths of all MOD buffers

Jia - LANL

PLD STO

Emphasized chemical & thermal stability; lattice match to YBCO

PLD YBCO/STO/IBAD MgO

Single layer YBCO = 400 A/cm (~ 1.5 micron thick)

Multiple layer YBCO/CeO₂ = 660 - 1400 A/cm (~ 1.7 - 3.6 micron thick)

PAD: Polymer Assisted Deposition

Simple, low cost, non-vacuum buffer process

HRTEM showed high quality films

Amenable to multi layers, complex oxides, thick films (100-1000 nm)

Directions

Implement PAD process in YBCO/IBAD architecture?

Clem - SNL

MOD STO

STO/CTO/NiW very promising

Good barrier (0.2 - 0.5 micron) to O₂ and substrate element diffusion

Good replication of substrate texture (~ 0.5 deg. Less)

AMSC YBCO/CeO₂ on STO/CTO/NiW

139A/cm (~ 0.8 micron thick)

Directions

Reduce RMS surface roughness

Continue to search for better lattice match buffers (goal: single material)